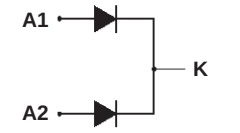
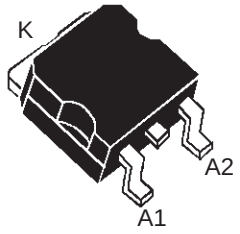
STPR1620CG

ULTRA FAST RECOVERY RECTIFIER DIODES

FEATURES

- SUITED FOR SMPS
- LOW LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIME
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- SMD PACKAGE





D^2PAK
(Plastic)

DESCRIPTION

Low cost dual center tap rectifier suited for switchmode power supply and high frequency DC to DC converters.
Packaged in D^2PAK this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE MAXIMUM (limiting values)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			200	V
$I_{F(RMS)}$	RMS forward current		Per diode	20	A
$I_{F(AV)}$	Average forward current $\delta = 0.5$	Tc=120°C	Per diode Per device	8 16	A
I_{FSM}	Surge non repetitive forward current	tp=10ms sinusoidal	Per diode	80	A
T_{stg} T_j	Storage temperature range Maximum junction temperature			- 65 to + 150 150	°C °C

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th\ (j-c)}$	Junction to case	Per diode	3.0	°C/W
		Total		
$R_{th\ (c)}$	Coupling			°C/W

When the diodes 1 and 2 are used simultaneously :
Δ Tj(diode 1) = P(diode 1) x Rth(j-c) (Per diode) + P(diode 2) x Rth(c)

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I_R *	T_j = 25°C	$V_R = V_{RRM}$			50	µA
	T_j = 100°C				0.6	mA
V_F **	T_j = 125°C	I_F = 8 A			0.99	V
	T_j = 125°C	I_F = 16 A			1.20	
	T_j = 25°C	I_F = 16 A			1.25	

Pulse test : * tp = 5 ms, duty cycle < 2 %
** tp = 380 µs, duty cycle < 2 %

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
trr	T_j = 25°C	I_F = 0.5A Irr = 0.25A I_R = 1A			30	ns
tfr	T_j = 25°C	I_F = 1A tr = 10 ns $V_{FR} = 1.1 \times V_F$		20		ns
V_{FP}	T_j = 25°C	I_F = 1A tr = 10 ns		3		V

To evaluate the conduction losses use the following equation :
$P = 0.78 \times I_{F(AV)} + 0.026 \times I_{F^2(RMS)}$

Fig.1 : Average forward power dissipation versus average forward current (Per diode).

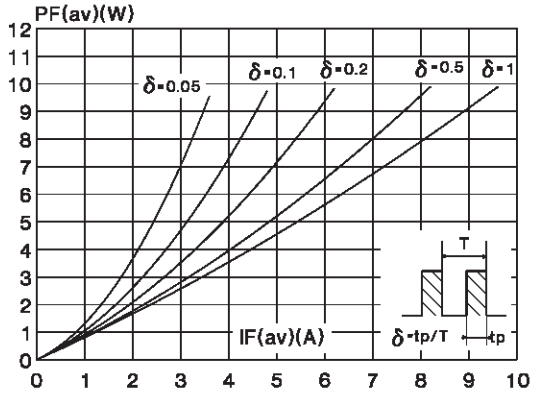


Fig.2 : Peak current versus form factor.(Per diode)

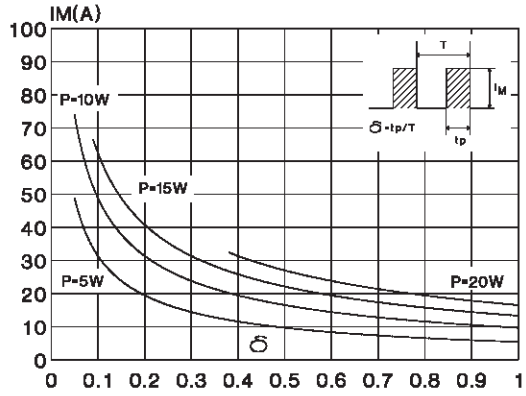


Fig.3 : Average current versus ambient temperature. (duty cycle : 0.5) (Per diode)

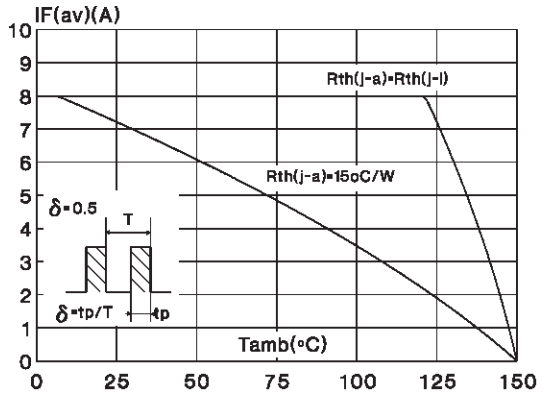


Fig.4 : Non repetitive surge peak forward current versus overload duration (Maximum values) (Per diode).

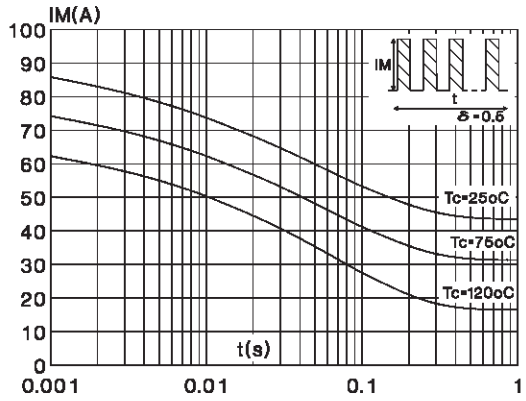


Fig.5 : Relative variation of thermal transient impedance junction to case versus pulse duration (Per diode).

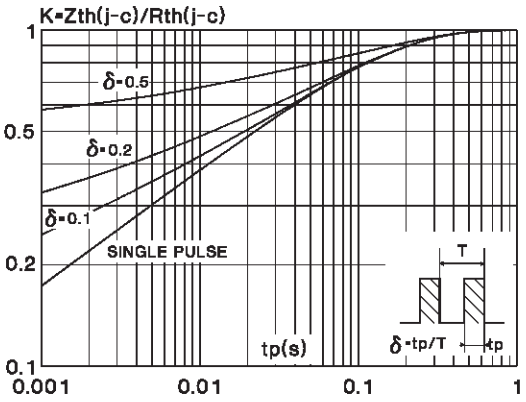


Fig.6 : Forward voltage drop versus forward current. (maximum values) (Per diode).

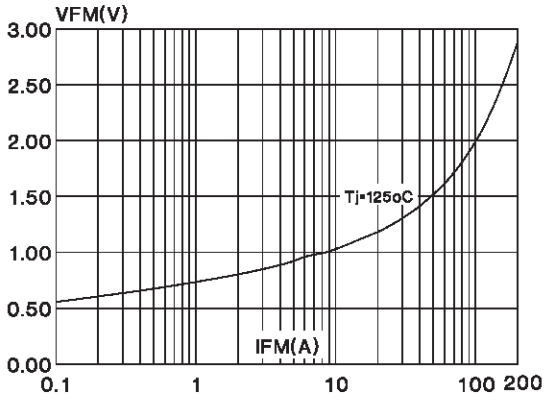


Fig.7 : Junction capacitance versus reverse voltage applied (Typical values) (Per diode).

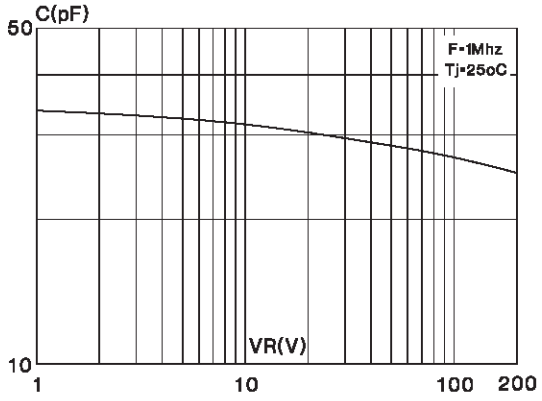


Fig.8 : Recovery charges versus dIF/dt (Per diode).

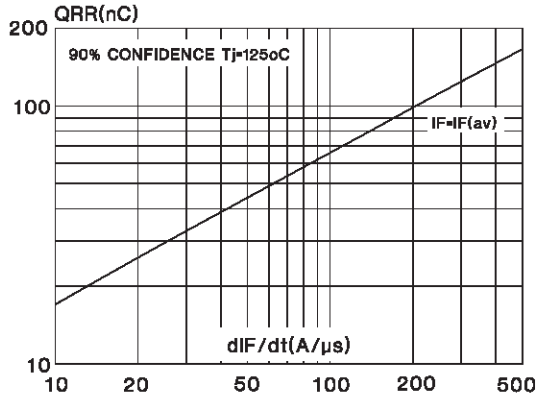


Fig.9 : Peak reverse current versus dIF/dt (Per diode).

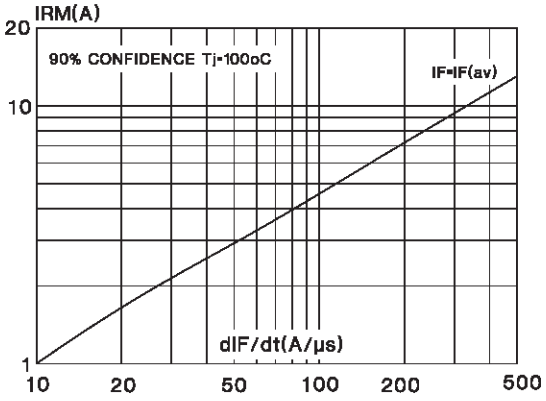
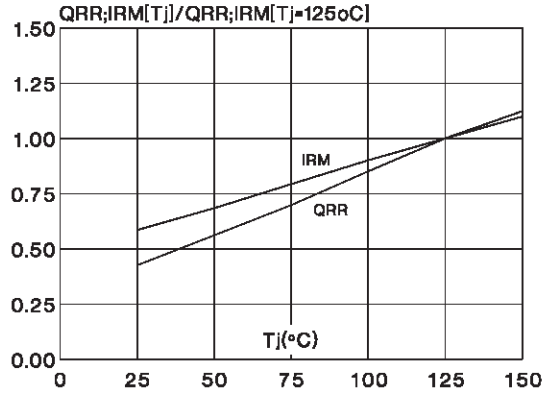
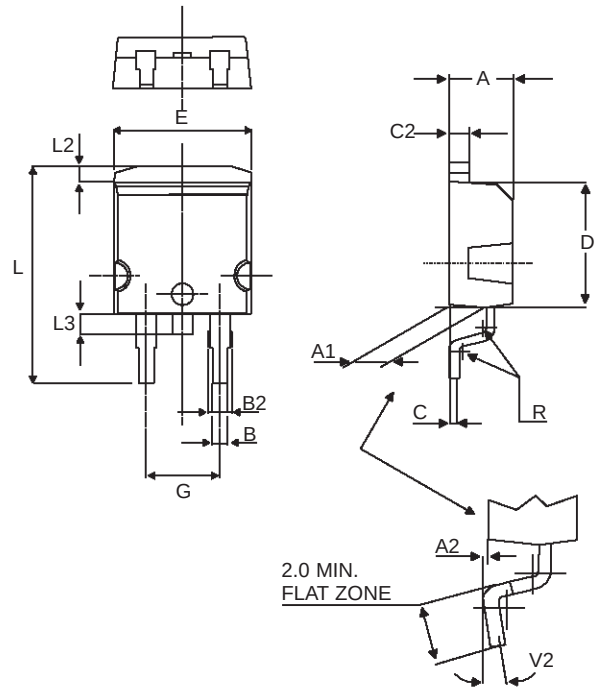


Fig.10 : Dynamic parameters versus junction temperature (Per diode).



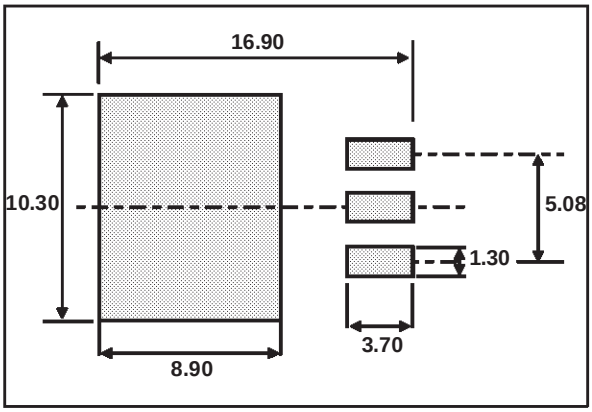
PACKAGE MECHANICAL DATA

D^2PAK (Plastic)



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.70		0.93	0.027		0.037
B2	1.25	1.40		0.049	0.055	
C	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	8.95		9.35	0.352		0.368
E	10.00		10.28	0.393		0.405
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.40	0.050		0.055
L3	1.40		1.75	0.055		0.069
R		0.40			0.016	
V2	0°		8°	0°		8°

FOOT PRINT (in millimeters)



- **Marking** : Type number
- Cooling method : C
- Weight : 1.8 g